

## Silicon NPN Power Transistors

2SC4927

## DESCRIPTION

- With TO-3PFM package
- Built-in damper diode
- High breakdown voltage

## APPLICATIONS

- TV/Character display horizontal deflection output applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

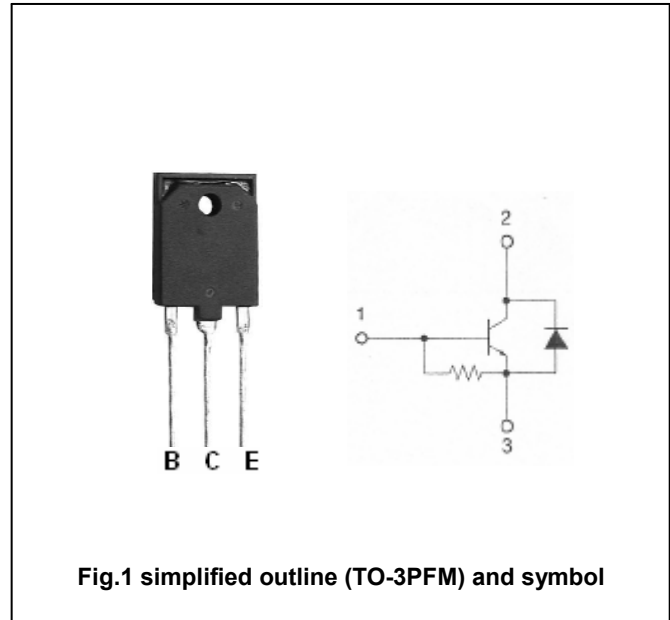


Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CEO}$	Collector-emitter voltage	Open base	1500	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		8	A
$I_{C(peak)}$	Collector current-peak		9	A
$I_{C(surge)}$	Collector current-surge		18	A
$I_o$	C to E diode forward current		8	A
$P_C$	Collector power dissipation	$T_C = 25 \square$	50	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-55~150	$\square$

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=500mA ; I_C=0$	6			V
$I_{CES}$	Collector cut-off current	$V_{CE}=1500V ; R_{BE}=0$			0.5	mA
$h_{FE}$	DC current gain	$I_C=1A ; V_{CE}=5V$			25	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			1.5	V
$V_{ECF}$	Diode forward voltage	$I_F=8A$			2.0	V
$t_f$	Fall time	$I_{CP}=6A ; f_H=31.5kHz$ $I_{B1}=1.2A ; I_{B2}=-2.4A$			0.5	μs

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PACKAGE OUTLINE

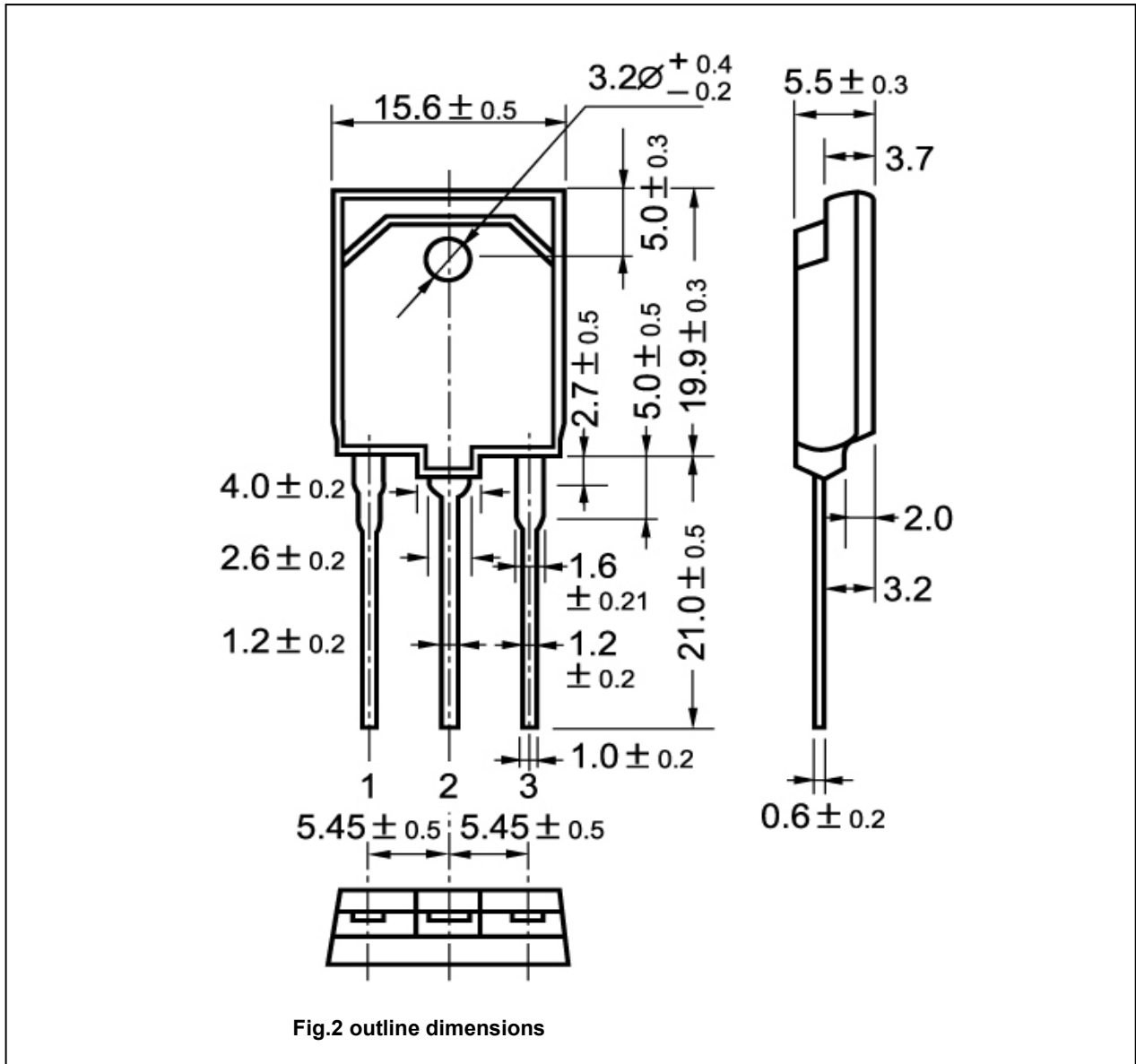


Fig.2 outline dimensions

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